

<b>Interview Summary</b>	<b>Application No.</b>		<b>Applicant(s)</b>	
	09/196,789		LYONS ET AL.	
	<b>Examiner</b>		<b>Art Unit</b>	
	Anh D. Mai		2814	

All participants (applicant, applicant's representative, PTO personnel):

(1) Anh D. Mai. (3) \_\_\_\_\_.

(2) Deb Lou. (4) \_\_\_\_\_.

Date of Interview: 30 August 2001.

Type: a) ☒ Telephonic b) ☐ Video Conference  
c) ☐ Personal [copy given to: 1) ☐ applicant 2) ☐ applicant's representative]

Exhibit shown or demonstration conducted: d) ☐ Yes e) ☒ No.

If Yes, brief description: \_\_\_\_\_.

Claim(s) discussed: 1 and 30.

Identification of prior art discussed: \_\_\_\_\_.

Agreement with respect to the claims f) ☐ was reached. g) ☐ was not reached. h) ☒ N/A.

Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: applicant states that as oppose to the prior art technique, the present invention use one etch process to form the trench. However, the terminology used also includes a single etch recipe to remove the composition mask and the silicon substrate without the photoresist layer. Further, the non-selective etch does not appear to be working since the trench opening will not be as small as the original mask opening using a single, continuous etch process.

(A fuller description, if necessary, and a copy of the amendments which the examiner agreed would render the claims allowable, if available, must be attached. Also, where no copy of the amendments that would render the claims allowable is available, a summary thereof must be attached.)

i) ☐ It is not necessary for applicant to provide a separate record of the substance of the interview(if box is checked).

Unless the paragraph above has been checked, THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN ONE MONTH FROM THIS INTERVIEW DATE TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.

Examiner Note: You must sign this form unless it is an Attachment to a signed Office action.

\_\_\_\_\_  
Examiner's signature, if required



US005763021A

**United States Patent** [19]

Young et al.

[11] **Patent Number:** 5,763,021[45] **Date of Patent:** Jun. 9, 1998[54] **METHOD OF FORMING A DIELECTRIC FILM**[75] **Inventors:** Andrew W. Young, Georgetown; Don D. Smith, Round Rock, both of Tex.[73] **Assignee:** Cypress Semiconductor Corporation, San Jose, Calif.

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**OTHER PUBLICATIONS**

*J. Electrochem. Soc.* vol. 143, No. 6, Jun., 1996 Dielectric Constant and Stability of Fluorine-Doped Plasma Enhanced Chemical Vapor Deposited SiO Thin Films, Peter W. Lee, Shinsuke Mizuno, Amrita Verma, Huyen Tran and Bang Nguyen.

*Primary Examiner*—Bernard Pianalto  
*Attorney, Agent, or Firm*—Oblon, Spivak, McClelland, Maier & Neustadt, P.C.

[21] **Appl. No.:** 766,608[22] **Filed:** Dec. 13, 1996[51] **Int. Cl.<sup>6</sup>** ..... H05H 1/24[52] **U.S. Cl.** ..... 427/579; 427/255.2; 427/255.3; 427/294; 427/585[58] **Field of Search** ..... 427/579, 585, 427/255.2, 255.3, 294[56] **References Cited****U.S. PATENT DOCUMENTS**

4,579,571	4/1986	Hicks	65/3.12
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[57] **ABSTRACT**

The present invention relates to a method of forming a dielectric film, a semiconductor device comprising the same, a method of operating a plasma enhanced chemical vapor deposition apparatus and a method of manufacturing a semiconductor device comprising the dielectric film.

**15 Claims, No Drawings**